

### **Amendments to the Specification**

***Please replace the paragraph beginning on page 2, line 15 with the following amended paragraph:***

A semiconductor device that has an improved noise shielding feature has been described in Japanese Patent Laid-Open No. 2000-235979. The semiconductor device disclosed in this reference has a ground layer which is formed between the semiconductor chip and the redistribution wirings.

***Please replace the paragraph beginning on page 2, line 19 with the following amended paragraph:***

However, an additional process for forming the ground layer is needed in the semiconductor device disclosed in the reference. Also, the ground layer increases a thickness of the semiconductor device.

***Please replace the paragraph beginning on page 6, line 16 with the following amended paragraph:***

The metal member 150 is located above the capacitor 101 so that the metal member 150 covers the entire capacitor 101 as shown in Fig. 2. The redistribution wirings 500 or the external terminals 400 which are applied the high frequency signal are formed above the metal member 150. The metal member 150 shields the capacitor 101 from noise generated by the redistribution wirings 500 or the external terminals

400. Further, the metal member 150 is connected to ~~[[the]]~~ an electrode pad 200 which is applied with a ground voltage.

***Please replace the paragraph beginning on page 8, line 5 with the following amended paragraph:***

The capacitor 101 is a part of the electronic circuit. For example, the capacitor may be used to determine an oscillation frequency of the VCO ~~[[VOC]]~~. A voltage swing in the external terminals 400 or the redistribution wirings 500 generates the noise. In the conventional semiconductor device, a capacitance value in the capacitor might be changed by the electromagnetic induction which is caused by the noise. The telecommunication device is operated by high frequency. Therefore, a communication characteristic of the semiconductor device is easily changed by the noise.

***Please replace the paragraph beginning on page 11, line 3 with the following amended paragraph:***

First, the electronic element such as the capacitor is formed on the semiconductor substrate. Then, the insulating layer 130a is formed on the semiconductor substrate 110 and the wirings 140a are formed on the interlayer insulating layer 130a as shown in Fig. 9. Then, the wirings 140b and the metal member 150 are formed on the interlayer insulating layer ~~[[130a]]~~ 130b, as shown in Fig. 10.

***Please replace the paragraph beginning on page 15, line 4 with the following amended paragraph:***

The insulating layer 340 and the insulating layer ~~[[340]]~~ 330 are formed of polyimide. The magnetic material 800a and the magnetic material 800b are formed of Fe(iron), Ni(nickel) or Co(cobalt).

***Please replace the paragraph beginning on page 15, line 7 with the following amended paragraph:***

The magnetic material 800b is arranged under the inductor 900b and the inductor ~~[[900b]]~~ 900a is arranged under the magnetic material 800a.